

**GE50L02****N-CHANNEL ENHANCEMENT MODE POWER MOSFET**

BVDSS	25V
RDS(ON)	17mΩ
ID	40A

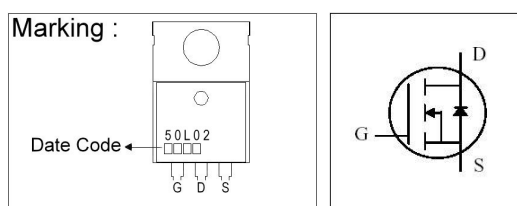
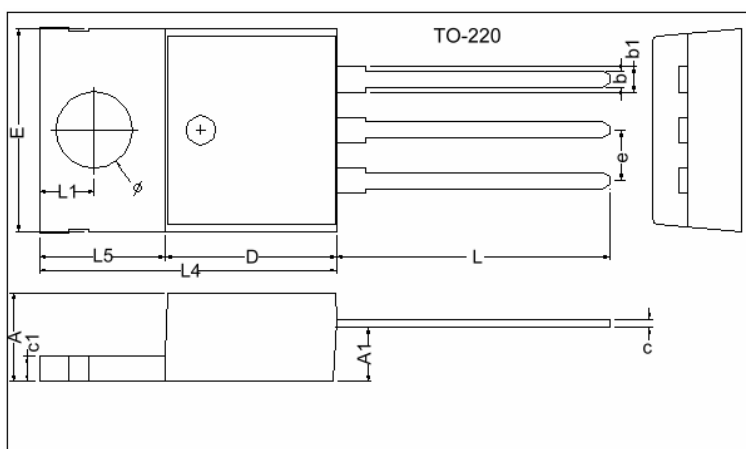
**Description**

The GE50L02 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The through-hole version (TO-220) is available for low-profile applications and suited for low voltage applications such as DC/DC converters.

**Features**

- \*Low Gate Charge
- \*Simple Drive Requirement
- \*Fast Switching Characteristic

**Package Dimensions**

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.40	4.80	c1	1.25	1.45
b	0.76	1.00	b1	1.17	1.47
c	0.36	0.50	L	13.25	14.25
D	8.60	9.00	e	2.54 REF.	
E	9.80	10.4	L1	2.60	2.89
L4	14.7	15.3	Ø	3.71	3.96
L5	6.20	6.60	A1	2.60	2.80

**Absolute Maximum Ratings**

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	$V_{DS}$	25	V
Gate-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=25^{\circ}C$	40	A
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=100^{\circ}C$	27	A
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	140	A
Total Power Dissipation	$P_D @T_C=25^{\circ}C$	44.6	W
Linear Derating Factor		0.36	W/°C
Operating Junction and Storage Temperature Range	$T_j, T_{stg}$	-55 ~ +150	°C

**Thermal Data**

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-case Max.	$R_{thj-c}$	2.8	°C/W
Thermal Resistance Junction-ambient Max.	$R_{thj-a}$	62	°C/W

**Electrical Characteristics (T<sub>j</sub> = 25°C unless otherwise specified)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	25	-	-	V	V <sub>GS</sub> =0, I <sub>D</sub> =250uA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS} / \Delta T_j$	-	0.037	-	V/°C	Reference to 25°C, I <sub>D</sub> =1mA
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	-	3.0	V	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA
Forward Transconductance	g <sub>fs</sub>	-	10	-	S	V <sub>DS</sub> =10V, I <sub>D</sub> =20A
Gate-Source Leakage Current	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> = ±20V
Drain-Source Leakage Current(T <sub>j</sub> =25°C)	I <sub>DSS</sub>	-	-	1	uA	V <sub>DS</sub> =25V, V <sub>GS</sub> =0
Drain-Source Leakage Current(T <sub>j</sub> =150°C)		-	-	25	uA	V <sub>DS</sub> =20V, V <sub>GS</sub> =0
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	-	17	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =20A
		-	-	35		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A
Total Gate Charge <sup>2</sup>	Q <sub>g</sub>	-	11.5	-	nC	I <sub>D</sub> =20A V <sub>DS</sub> =20V V <sub>GS</sub> =5V
Gate-Source Charge	Q <sub>gs</sub>	-	2.1	-		
Gate-Drain ("Miller") Charge	Q <sub>gd</sub>	-	8.4	-		
Turn-on Delay Time <sup>2</sup>	T <sub>d(on)</sub>	-	7	-	ns	V <sub>DS</sub> =15V I <sub>D</sub> =20A V <sub>GS</sub> =10V R <sub>G</sub> =3.3Ω R <sub>D</sub> =0.75Ω
Rise Time	T <sub>r</sub>	-	60	-		
Turn-off Delay Time	T <sub>d(off)</sub>	-	17	-		
Fall Time	T <sub>f</sub>	-	9	-		
Input Capacitance	C <sub>iss</sub>	-	390	-	pF	V <sub>GS</sub> =0V V <sub>DS</sub> =25V f=1.0MHz
Output Capacitance	C <sub>oss</sub>	-	245	-		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	100	-		

**Source-Drain Diode**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage <sup>2</sup>	V <sub>SD</sub>	-	-	1.26	V	I <sub>S</sub> =40A, V <sub>GS</sub> =0V, T <sub>j</sub> =25°C
Continuous Source Current (Body Diode)	I <sub>S</sub>	-	-	40	A	V <sub>D</sub> =V <sub>G</sub> =0V, V <sub>S</sub> =1.26V
Pulse Source Current (Body Diode) <sup>1</sup>	I <sub>SM</sub>	-	-	140	A	

Notes: 1. Pulse width limited by safe operating area.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

## Characteristics Curve

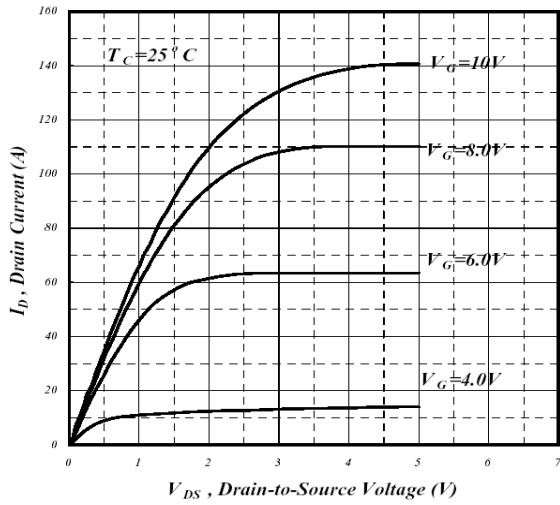


Fig 1. Typical Output Characteristics

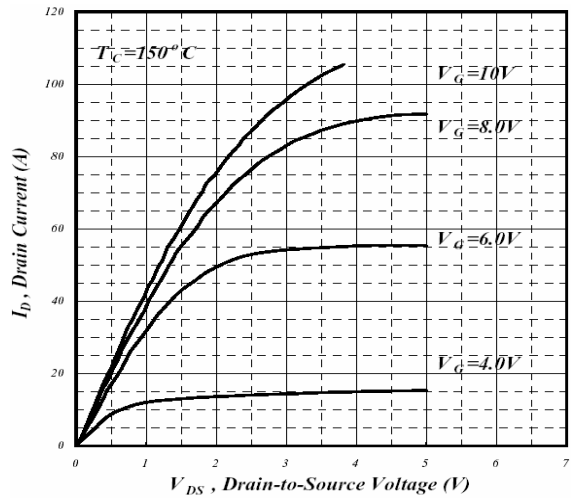


Fig 2. Typical Output Characteristics

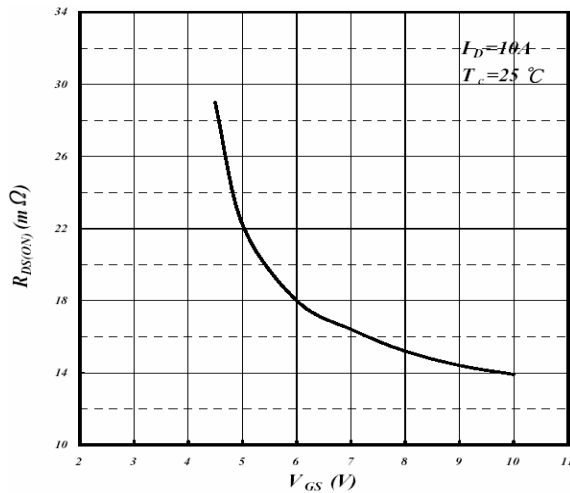


Fig 3. On-Resistance v.s. Gate Voltage

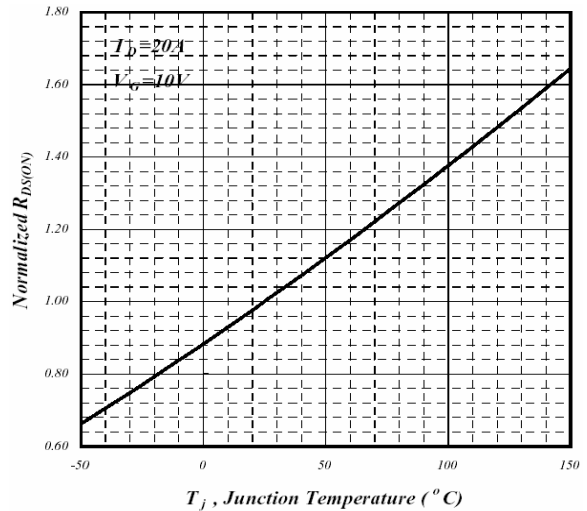


Fig 4. Normalized On-Resistance v.s. Junction Temperature

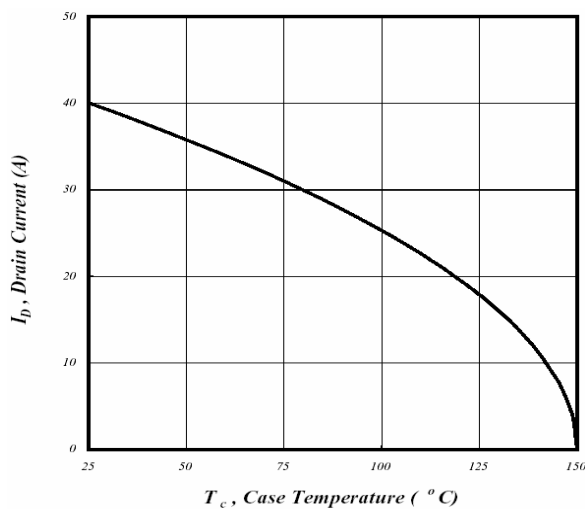


Fig 5. Maximum Drain Current v.s. Case Temperature

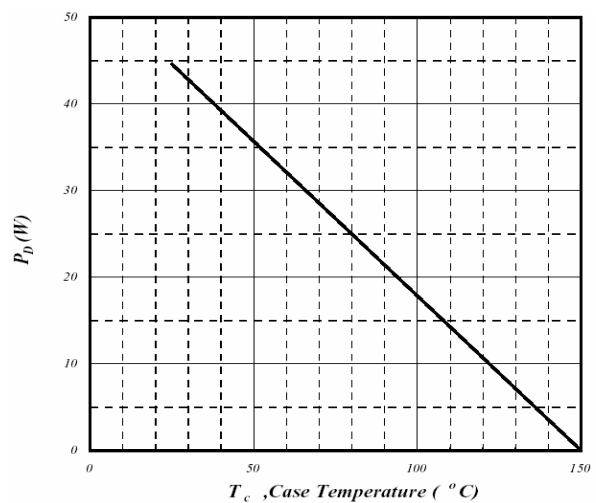
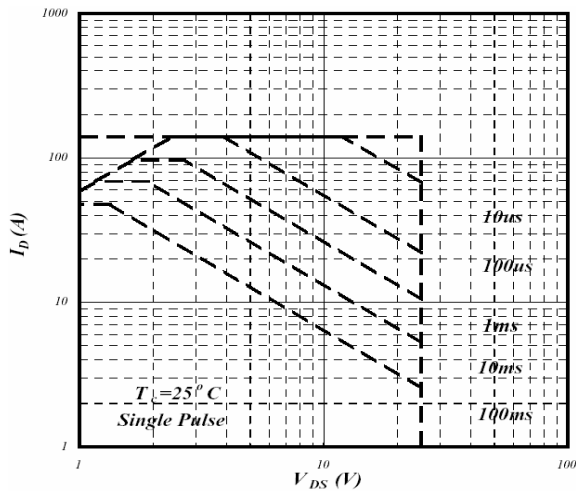
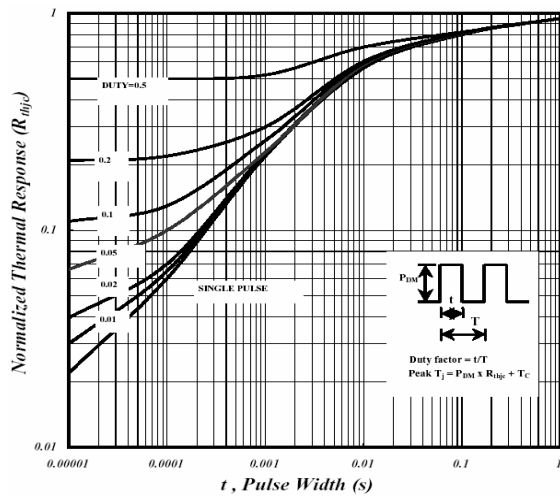


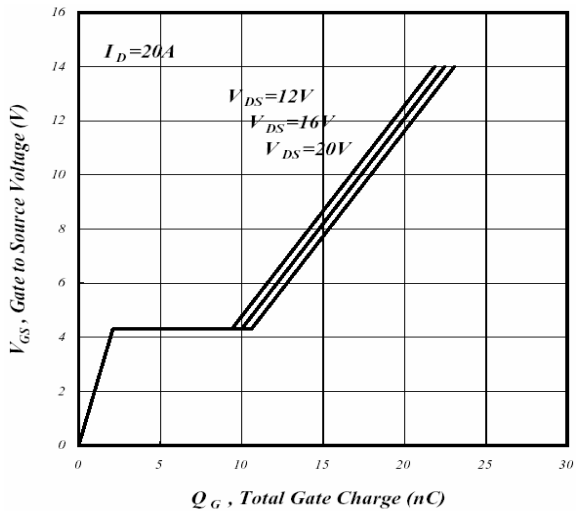
Fig 6. Type Power Dissipation



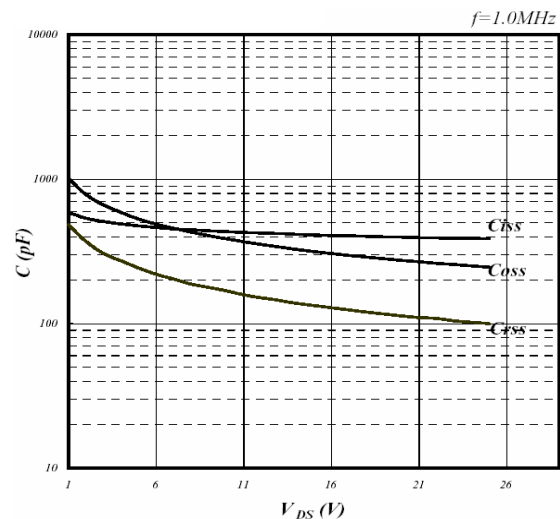
**Fig 7. Maximum Safe Operating Area**



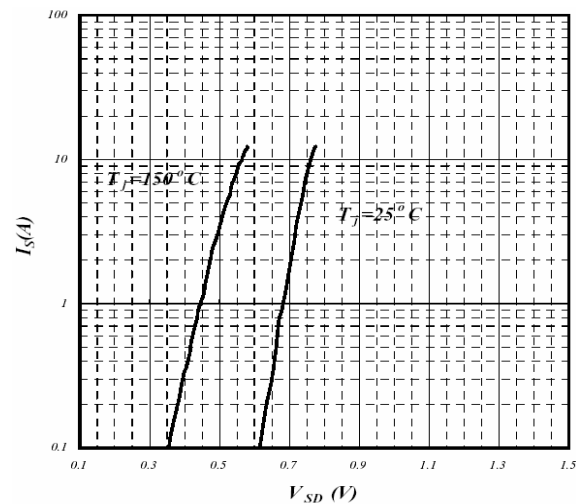
**Fig 8. Effective Transient Thermal Impedance**



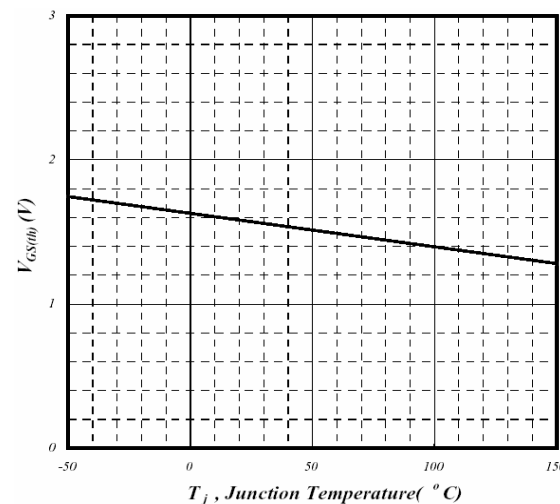
**Fig 9. Gate Charge Characteristics**



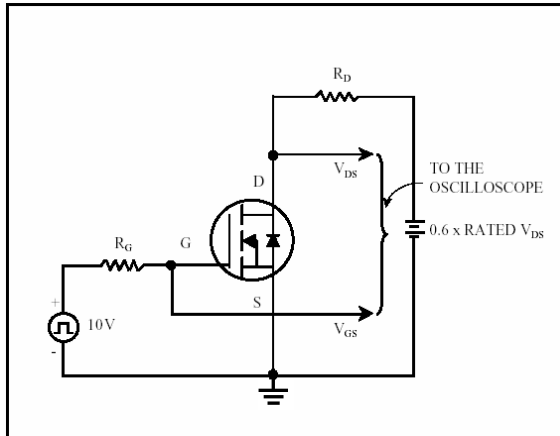
**Fig 10. Typical Capacitance Characteristics**



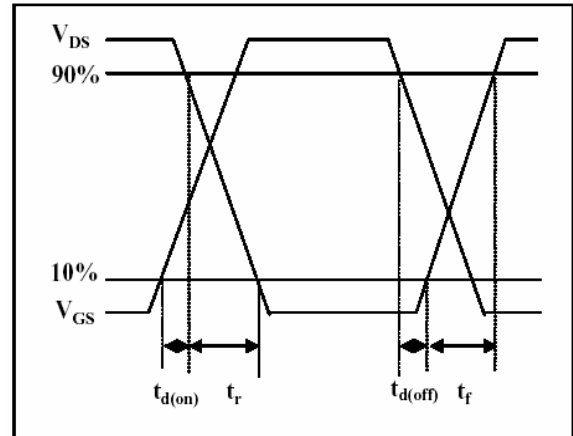
**Fig 11. Forward Characteristics of Reverse Diode**



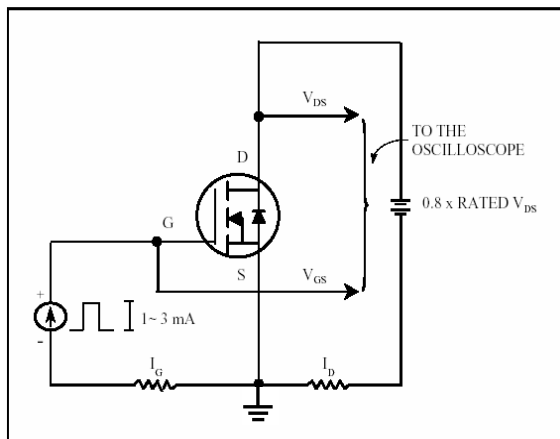
**Fig 12. Gate Threshold Voltage v.s. Junction Temperature**



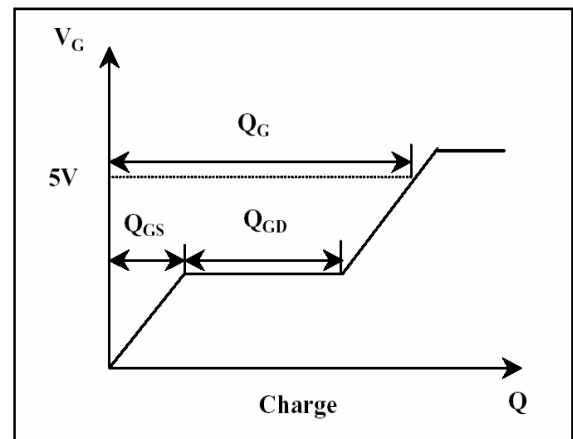
**Fig 13. Switching Time Circuit**



**Fig 14. Switching Time Waveform**



**Fig 15. Gate Charge Circuit**



**Fig 16. Gate Charge Waveform**

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